

Features

- Fast switching
- Low Gate Charge
- Improved dv/dt capability
- 100% avalanche tested
- Green Device Available

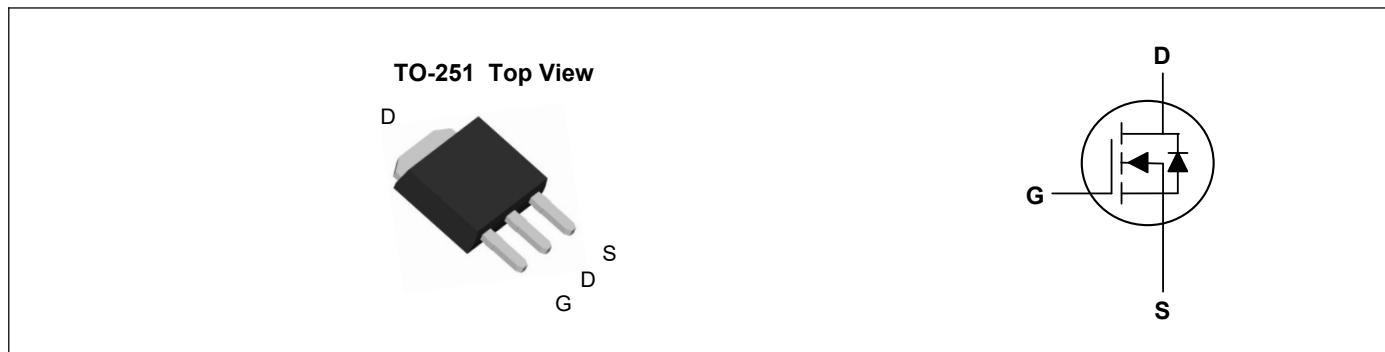
Product Summary



V_{DS}	650	V
I_D	5	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.8	Ω

Applications

- High Efficiency Switch Mode Power Supplies
- Electronic Lamp Ballasts
- UPS



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ¹	I_D	5	A
Continuous Drain Current ¹	I_D	3.2	A
Pulsed Drain Current ²	I_{DM}	20	A
Single Pulse Avalanche Energy ³	E_{AS}	252	mJ
Total Power Dissipation ⁴	P_D	90	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62.5	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	1.35	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	650	---	---	V
Static Drain-Source On-Resistance ²	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=2.5\text{A}$	---	2.4	2.8	Ω
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$	2	---	4	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=650\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{\text{DS}}=480\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 30\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Total Gate Charge	Q_g	$V_{\text{DS}}=480\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=5\text{A}$	---	14.3	---	nC
Gate-Source Charge	Q_{gs}		---	2.9	---	
Gate-Drain Charge	Q_{gd}		---	6.3	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=300\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=25\Omega$, $I_D=5\text{A}$	---	15.7	---	ns
Rise Time	T_r		---	37.3	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	39.7	---	
Fall Time	T_f		---	31.3	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=25\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	480	---	pF
Output Capacitance	C_{oss}		---	61	---	
Reverse Transfer Capacitance	C_{rss}		---	5.7	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I_s	$T_c=25^\circ\text{C}$	---	---	5	A
Pulsed Source Current ²	I_{SM}		---	---	20	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=5\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.5	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=50\text{V}$, $V_{\text{GS}}=10\text{V}$, $L=30\text{mH}$
- 4.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

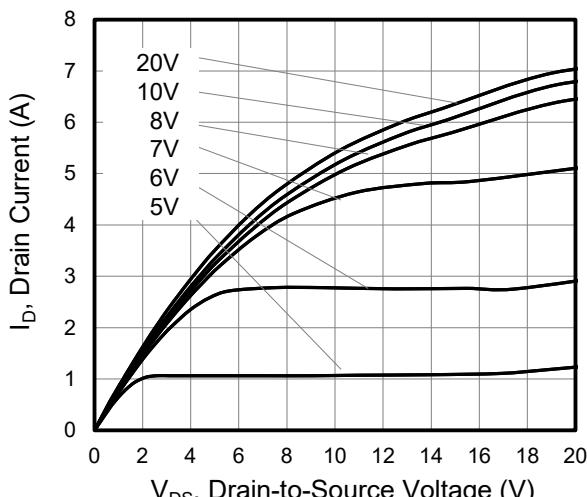


Figure 1. Output Characteristics

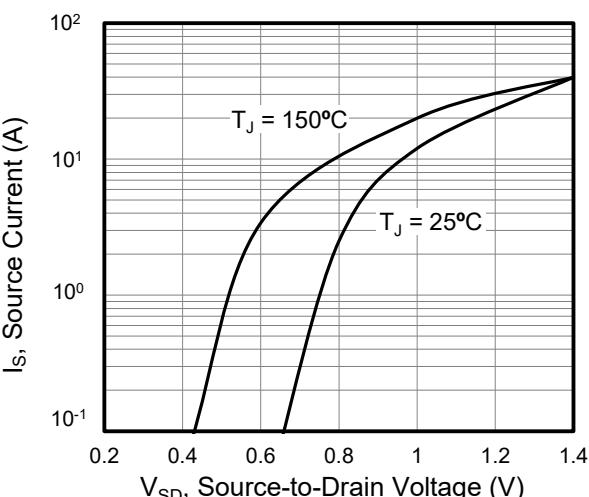


Figure 2. Body Diode Forward Voltage

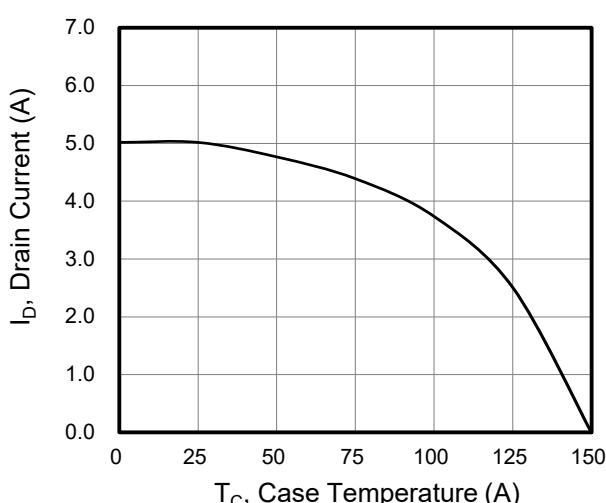


Figure 3. Drain Current vs. Temperature

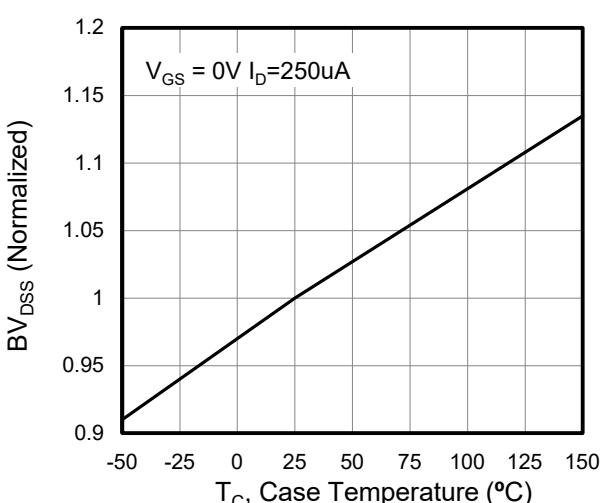


Figure 4. BV_{DSS} Variation vs. Temperature

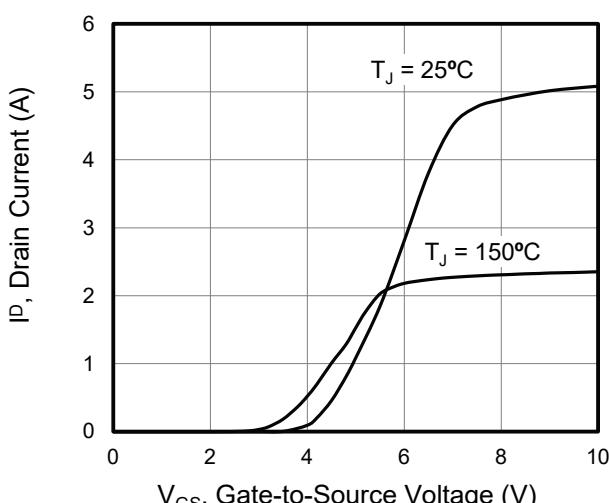


Figure 5. Transfer Characteristics

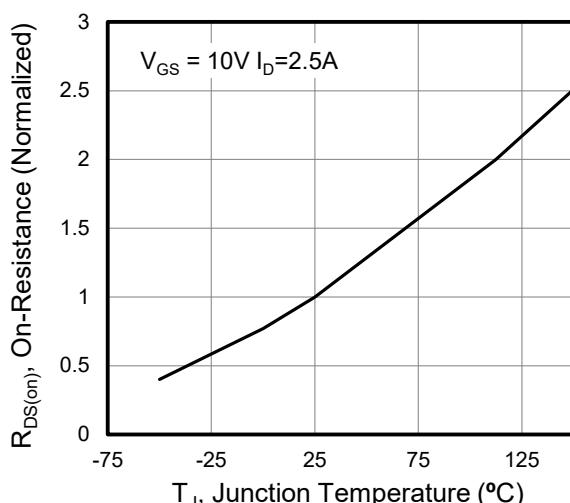
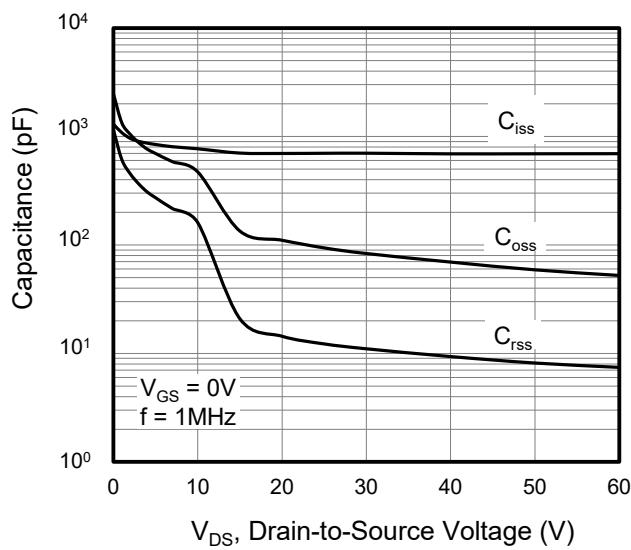
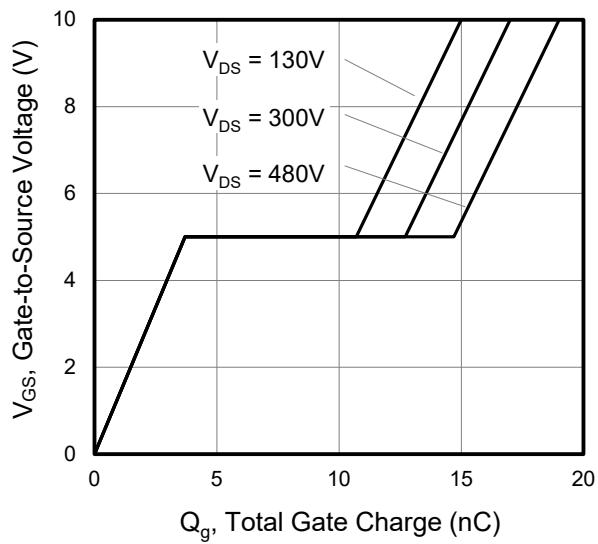
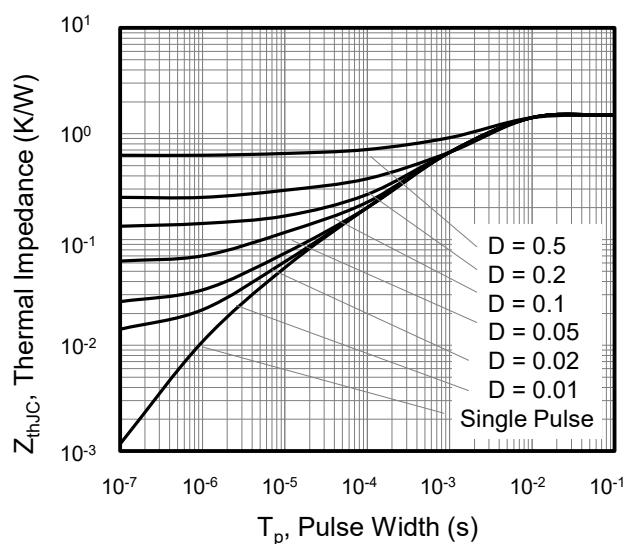
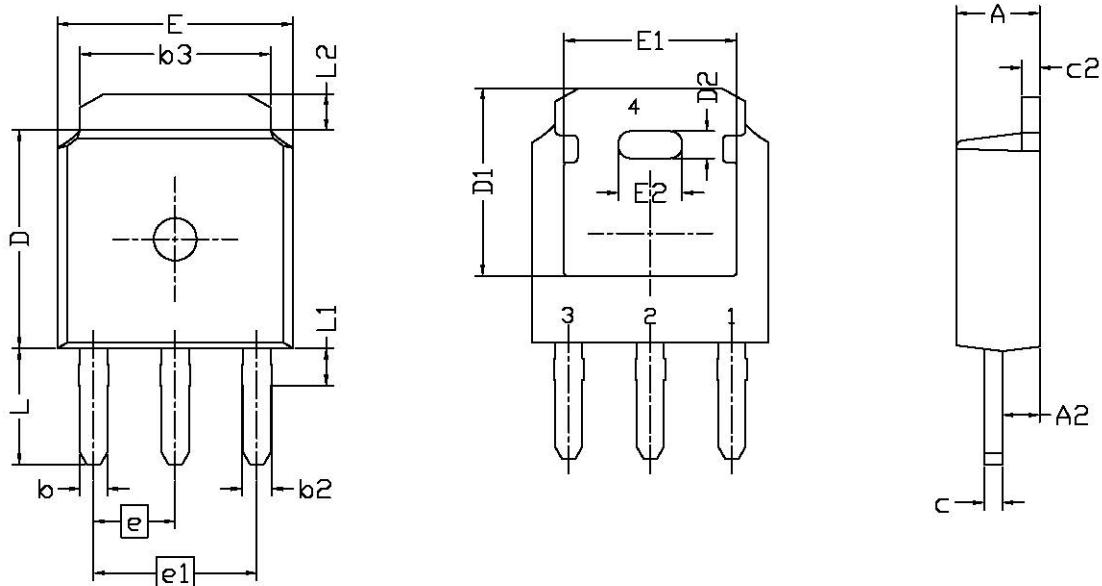


Figure 6. On-Resistance vs. Temperature


Figure 7. Capacitance

Figure 8. Gate Charge

Figure 9. Transient Thermal Impedance

TO-251 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	2.20	2.30	2.39	A2	0.90	1.00	1.14
b	0.63	0.76	0.85	b2	0.76	0.85	1.05
b3	5.10	5.40	5.60	C	0.46	0.51	0.61
C2	0.46	0.51	0.61	D	5.90	6.10	6.30
D1	5.25 REF			D2	0.508 BSC		
E	6.35	6.55	6.70	E1	5.06 REF		
E2	1.524 BSC			e	2.29 BSC		
e1	4.57 BSC			L	3.70	4.00	4.40
L1	1.15 REF			L2	0.90	1.06	1.20